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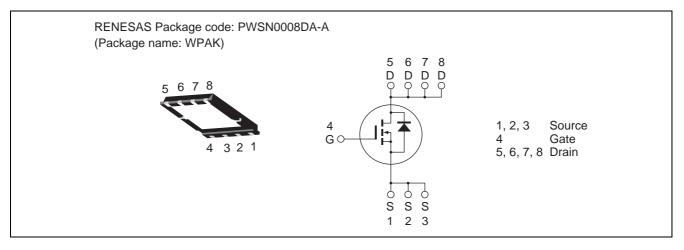
RJK0346DPA Silicon N Channel Power MOS FET Power Switching

> REJ03G1642-0200 Rev.2.00 Apr 10, 2008

# Features

- High speed switching
- Capable of 4.5 V gate drive
- Low drive current
- High density mounting
- Low on-resistance
  - $R_{DS(on)} = 1.5 \text{ m}\Omega \text{ typ.} (at V_{GS} = 10 \text{ V})$
- Pb-free

# Outline



# **Absolute Maximum Ratings**

			$(Ta = 25^{\circ}C)$	
Item	Symbol	Ratings	Unit	
Drain to source voltage	V <sub>DSS</sub>	30	V	
Gate to source voltage	V <sub>GSS</sub>	±20	V	
Drain current	ID	65	А	
Drain peak current	Note1 I <sub>D(pulse)</sub>	260	А	
Body-drain diode reverse drain current	I <sub>DR</sub>	65	А	
Avalanche current	I <sub>AP</sub> Note 2	35	А	
Avalanche energy	E <sub>AR</sub> Note 2	122.5	mJ	
Channel dissipation	Pch Note3	65	W	
Channel to Case Thermal Resistance	θch-C	1.92	°C/W	
Channel temperature	Tch	150	°C	
Storage temperature	Tstg	-55 to +150	°C	
			-	

Notes: 1.  $PW \le 10 \ \mu s$ , duty cycle  $\le 1\%$ 

2. Value at Tch = 25°C, Rg  $\ge$  50  $\Omega$ 

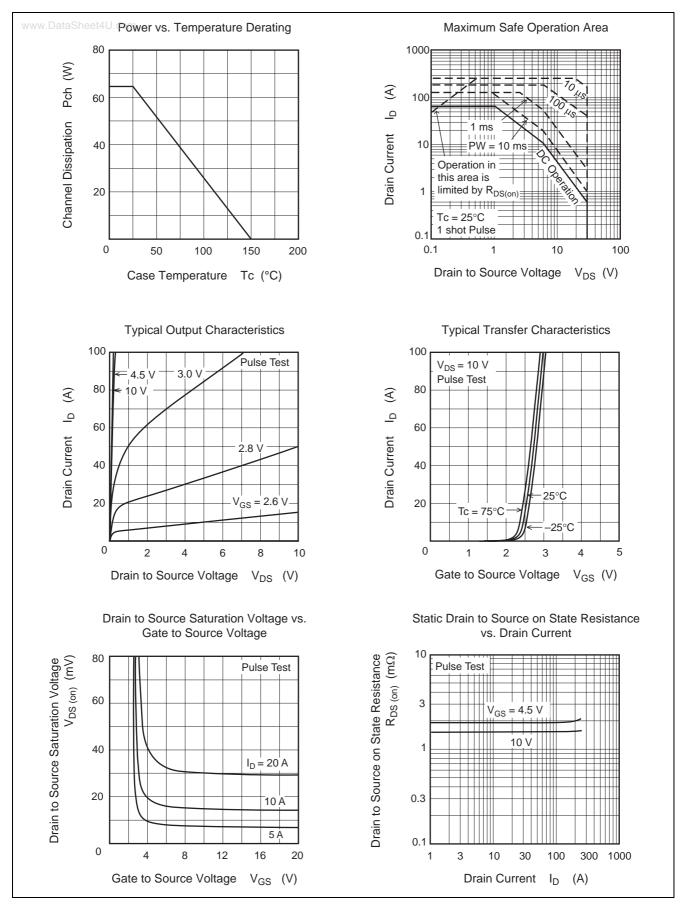
3. Tc = 25°C

# **Electrical Characteristics**

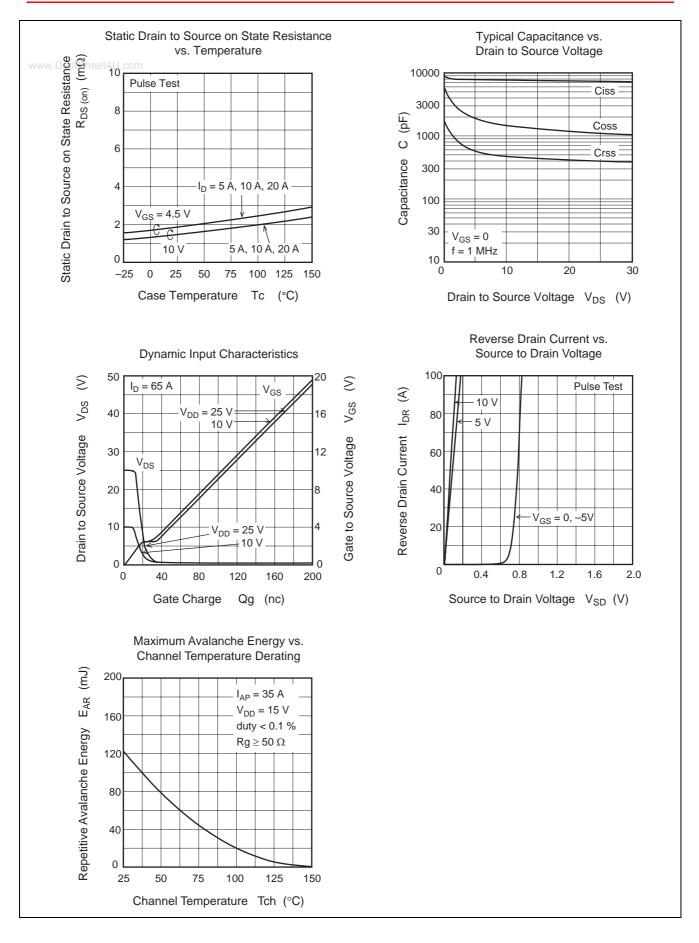
www.DataSheet4utem	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage	V <sub>(BR)DSS</sub>	30	_	_	V	$I_{D} = 10 \text{ mA}, V_{GS} = 0$
Gate to source leak current	I <sub>GSS</sub>		_	±0.1	μΑ	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I <sub>DSS</sub>		_	1	μΑ	$V_{DS} = 30 V, V_{GS} = 0$
Gate to source cutoff voltage	V <sub>GS(off)</sub>	1.2	_	2.5	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Static drain to source on state	R <sub>DS(on)</sub>	_	1.5	2.0	mΩ	$I_D = 32.5 \text{ A}, V_{GS} = 10 \text{ V}^{Note4}$
resistance	R <sub>DS(on)</sub>	_	1.9	2.7	mΩ	$I_D = 32.5 \text{ A}, V_{GS} = 4.5 \text{ V}^{\text{Note4}}$
Forward transfer admittance	y <sub>fs</sub>	_	130	—	S	$I_D = 32.5 \text{ A}, V_{DS} = 10 \text{ V}^{Note4}$
Input capacitance	Ciss	_	7650	_	pF	$V_{DS} = 10 \text{ V},  V_{GS} = 0,$ f = 1 MHz
Output capacitance	Coss	_	1500	—	pF	
Reverse transfer capacitance	Crss	_	470	—	pF	
Gate Resistance	Rg	_	1.2	—	Ω	
Total gate charge	Qg	_	49	—	nC	$V_{DD} = 10 \text{ V}, \text{ V}_{GS} = 4.5 \text{ V},$ $I_D = 65 \text{ A}$
Gate to source charge	Qgs	_	18.7	_	nC	
Gate to drain charge	Qgd	_	10.5	—	nC	
Turn-on delay time	t <sub>d(on)</sub>	_	15	—	ns	$V_{GS}$ = 10 V, $I_{D}$ = 32.5 A,
Rise time	tr	_	7	—	ns	$V_{\text{DD}} \cong 10 \text{ V}, \text{ R}_{\text{L}} = 0.31 \Omega,$ Rg = 4.7 $\Omega$
Turn-off delay time	t <sub>d(off)</sub>	_	86.5	_	ns	
Fall time	t <sub>f</sub>	_	20	_	ns	
Body-drain diode forward voltage	V <sub>DF</sub>	_	0.80	1.04	V	$I_F = 65 \text{ A}, V_{GS} = 0^{Note4}$
Body-drain diode reverse recovery	t <sub>rr</sub>	_	45	_	ns	$I_F = 65 \text{ A}, V_{GS} = 0$
time						di <sub>F</sub> / dt = 100 A/ μs

Notes: 4. Pulse test

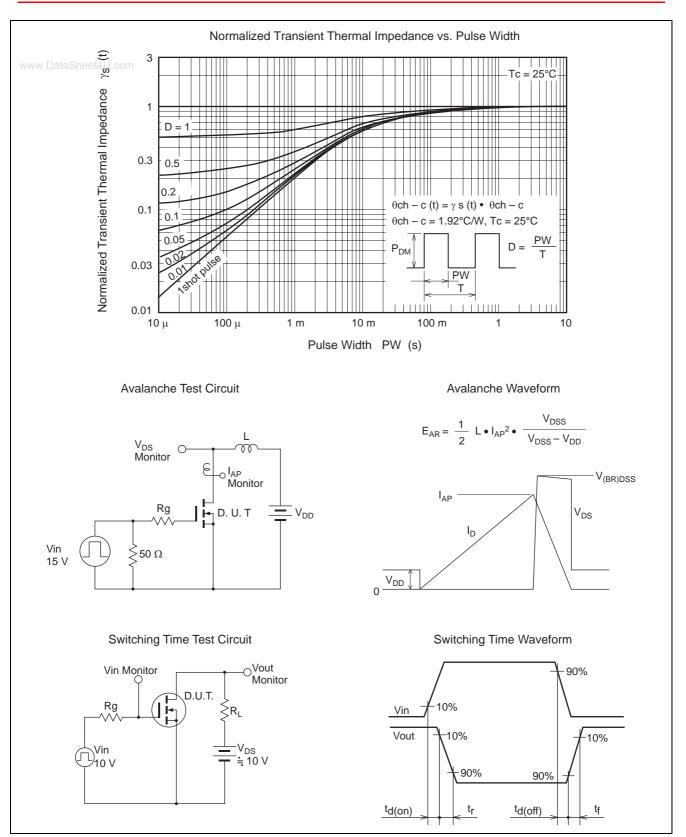
## **Main Characteristics**



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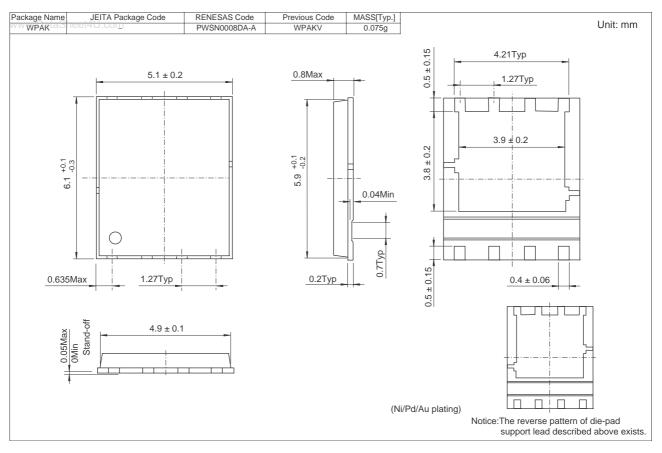


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# **Package Dimensions**



# **Ordering Information**

Part No.	Quantity	Shipping Container
RJK0346DPA-00-J0	2500 pcs	Taping

# RenesasTechnology Corp. sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

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450 Holger Way, San Jose, CA 95134-1368, U.S.A Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K. Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology (Shanghai) Co., Ltd. Unit 204, 205, AZIACenter, No.1233 Lujiazui Ring Rd, Pudong District, Shanghai, China 200120 Tel: <86> (21) 5877-1818, Fax: <86> (21) 6887-7858/7898

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Renesas Technology Taiwan Co., Ltd. 10th Floor, No.99, Fushing North Road, Taipei, Taiwan Tel: <886> (2) 2715-2888, Fax: <886> (2) 3518-3399

# Renesas Technology Singapore Pte. Ltd.

1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632 Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd. Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea Tel: <82> (2) 796-3115, Fax: <82> (2) 796-2145

Renesas Technology Malaysia Sdn. Bhd Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: <603> 7955-9390, Fax: <603> 7955-9510

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